

Green Products

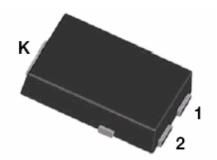
MBR860S SCHOTTKY RECTIFIER

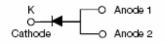
Applications:

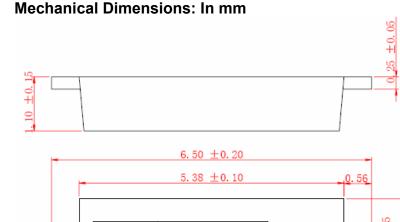
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

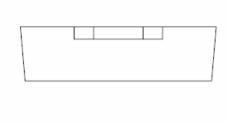
Features:

- Designed as Bypass Diodes for Solar Panels
- High Forward Surge Capability
- Ultra Low Forward Voltage Drop
- Excellent High Temperature Stability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request











TO-277B

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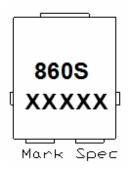
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Marking Diagram:



Where XXXXX is YYWWL

8 = Forward Current (8A) 60 = Reverse Voltage (60V)

S = Device Type

YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR860S	TO-277B (Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =80°C, rectangular wave form	8	А
Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	150	Α

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V_{F1}	@ 8A, Pulse, T _J = 25 °C	0.65	V
	V_{F2}	@ 8A, Pulse, T _J = 125 °C	0.60	V
Reverse Current	I _{R1}	$@V_R = rated V_R$	1.0	mA
		T _J = 25 °C		
	I_{R2}	$@V_R = rated V_R$	20	mA
		$T_J = 125^{\circ}C$		
Typical Junction	Cj	@V _R = 5.0 V, Tc=25℃	400	pF
Capacitance		fsig = 1MHz		

^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Soldering Point	$R_{\theta JS}$	DC operation	1.5	°C/W
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	2.3	°C/W
Approximate Weight	wt	-	0.08	g
Case Style		TO-277B		

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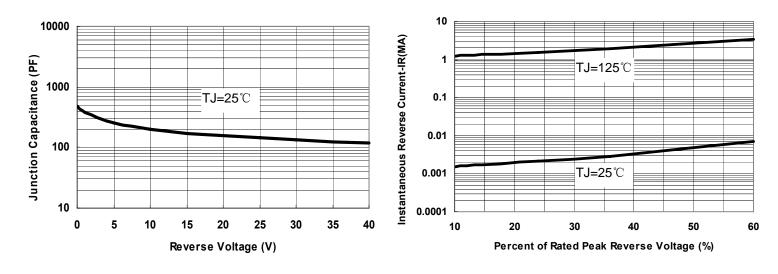


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

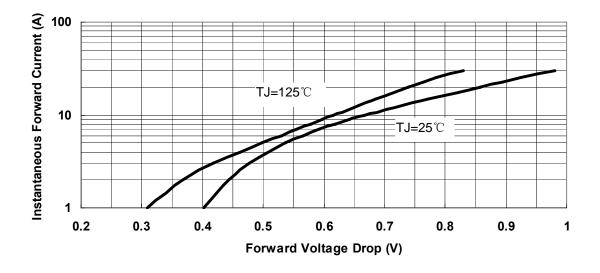


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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MBR860S

Technical Data Data Sheet N0029, Rev. A **Green Products**

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